

# BLF4G20LS-110B

UHF power LDMOS transistor

Rev. 01 — 10 January 2006

Product data sheet

## 1. Product profile

### 1.1 General description

110 W LDMOS power transistor for base station applications at frequencies from 1800 MHz to 2000 MHz.

**Table 1: Typical performance**

$f = 1930\text{ MHz to }1990\text{ MHz}$ ;  $T_{case} = 25\text{ }^{\circ}\text{C}$ ;  $I_{Dq} = 650\text{ mA}$ ; unless otherwise specified; in a class-AB production test circuit; typical values

Mode of operation	V <sub>DS</sub> (V)	P <sub>L</sub> (W)	G <sub>p</sub> (dB)	$\eta_D$ (%)	ACPR <sub>400</sub> (dBc)	ACPR <sub>600</sub> (dBc)	EVM <sub>rms</sub> (%)
CW	28	100	13.4	49	-	-	-
GSM EDGE	28	48 (AV)	13.8	38.5	-61 [1]	-74 [2]	2.1

[1] ACPR<sub>400</sub> at 30 kHz resolution bandwidth.

[2] ACPR<sub>600</sub> at 30 kHz resolution bandwidth.

### CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Therefore care should be taken during transport and handling.

### 1.2 Features

- Typical GSM EDGE performance at a frequency of 1930 MHz and 1990 MHz, a supply voltage of 28 V and an I<sub>Dq</sub> of 650 mA:
  - ◆ Load power = 48 W (AV)
  - ◆ Gain = 13.8 dB (typ)
  - ◆ Efficiency = 38.5 % (typ)
  - ◆ ACPR<sub>400</sub> = -61 dBc (typ)
  - ◆ ACPR<sub>600</sub> = -74 dBc (typ)
  - ◆ EVM<sub>rms</sub> = 2.1 % (typ)
- Easy power control
- Excellent ruggedness
- High efficiency
- Excellent thermal stability
- Designed for broadband operation (1800 MHz to 2000 MHz)
- Internally matched for ease of use

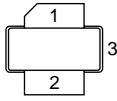

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### 1.3 Applications

- RF power amplifiers for GSM, GSM EDGE and CDMA base stations and multicarrier applications in the 1800 MHz to 2000 MHz frequency range.

## 2. Pinning information

**Table 2: Pinning**

Pin	Description	Simplified outline	Symbol
1	drain		 sym039
2	gate		
3	source		

[1] Connected to flange

## 3. Ordering information

**Table 3: Ordering information**

Type number	Package		
	Name	Description	Version
BLF4G20LS-110B	-	earless flanged LDMOST ceramic package; 2 leads	SOT502B

## 4. Limiting values

**Table 4: Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage		-	65	V
$V_{GS}$	gate-source voltage		-0.5	+15	V
$I_D$	drain current		-	12	A
$T_{stg}$	storage temperature		-65	+150	°C
$T_j$	junction temperature		-	200	°C

## 5. Thermal characteristics

**Table 5: Thermal characteristics**

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-case)}$	thermal resistance from junction to case	$T_{case} = 80\text{ °C}$				
		$P_L = 40\text{ W}$	-	0.62	0.71	K/W
		$P_L = 100\text{ W}$	-	0.52	0.61	K/W

## 6. Characteristics

**Table 6: Characteristics**

$T_j = 25^\circ\text{C}$  unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0\text{ V}; I_D = 0.9\text{ mA}$	65	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$V_{DS} = 10\text{ V}; I_D = 180\text{ mA}$	2.5	3.1	3.5	V
$V_{GSq}$	gate-source quiescent voltage	$V_{DS} = 28\text{ V}; I_D = 900\text{ mA}$	2.7	3.2	3.7	V
$I_{DSS}$	drain leakage current	$V_{GS} = 0\text{ V}; V_{DS} = 28\text{ V}$	-	-	3	$\mu\text{A}$
$I_{DSX}$	drain cut-off current	$V_{GS} = V_{GS(th)} + 6\text{ V};$ $V_{DS} = 10\text{ V}$	27	30	-	A
$I_{GSS}$	gate leakage current	$V_{GS} = \pm 15\text{ V}; V_{DS} = 0\text{ V}$	-	-	300	nA
$g_{fs}$	forward transconductance	$V_{DS} = 10\text{ V}; I_D = 10\text{ A}$	-	9.0	-	S
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 6\text{ V};$ $I_D = 6\text{ A}$	-	90	-	$\text{m}\Omega$
$C_{rs}$	feedback capacitance	$V_{GS} = 0\text{ V}; V_{DS} = 28\text{ V};$ $f = 1\text{ MHz}$	-	2.5	-	pF

## 7. Application information

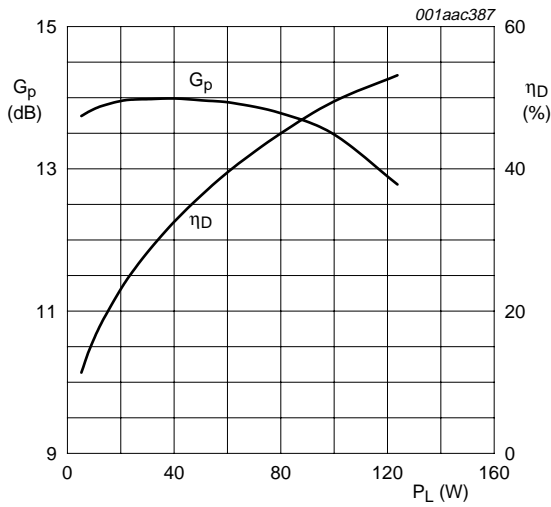
**Table 7: Application information**

Mode of operation: GSM EDGE;  $f = 1930\text{ MHz}$  and  $1990\text{ MHz}$ ; RF performance at  $V_{DS} = 28\text{ V}$ ;  $I_{Dq} = 650\text{ mA}$ ;  $T_{case} = 25^\circ\text{C}$ ; unless otherwise specified; in a class-AB production test circuit.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$G_p$	power gain	$P_{L(AV)} = 48\text{ W}$	13	13.8	-	dB
IRL	input return loss	$P_{L(AV)} = 48\text{ W}$	-	-10	-6.5	dB
$\eta_D$	drain efficiency	$P_{L(AV)} = 48\text{ W}$	36	38.5	-	%
$ACPR_{400}$	adjacent channel power ratio (400 kHz)	$P_{L(AV)} = 48\text{ W}$	-	-61	-58	dBc
$ACPR_{600}$	adjacent channel power ratio (600 kHz)	$P_{L(AV)} = 48\text{ W}$	-	-74	-71	dBc
$EVM_{rms}$	rms EDGE signal distortion error	$P_{L(AV)} = 48\text{ W}$	-	2.1	3.3	%
$EVM_M$	peak EDGE signal distortion error	$P_{L(AV)} = 48\text{ W}$	-	7.0	10	%

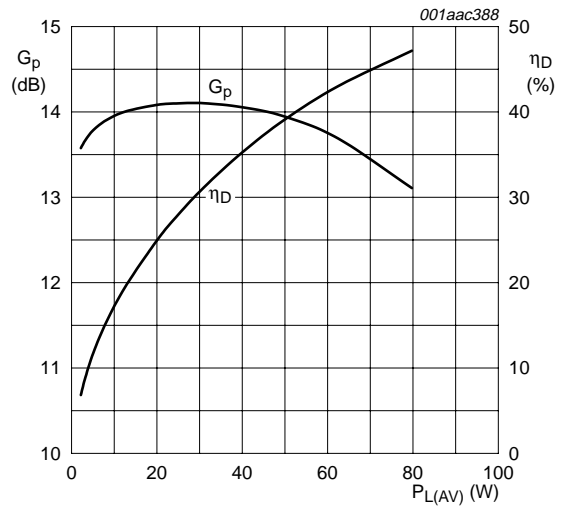
### 7.1 Ruggedness in class-AB operation

The BLF4G20LS-110B is capable of withstanding a load mismatch corresponding to  $V_{SWR} = 10 : 1$  through all phases under the following conditions:  $V_{DS} = 28\text{ V}$ ;  $I_{Dq} = 650\text{ mA}$ ;  $P_L = 110\text{ W}$  (CW);  $f = 1990\text{ MHz}$ .



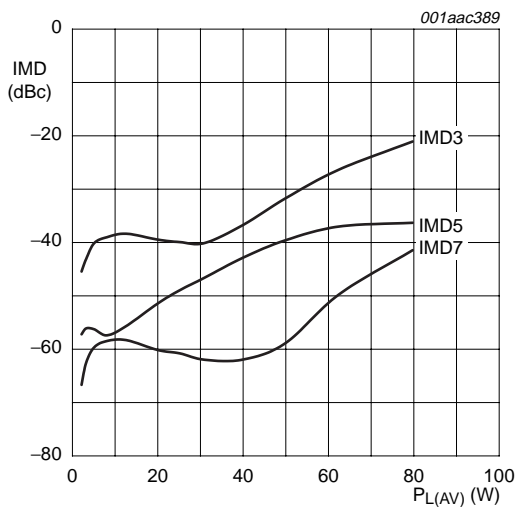
$V_{DS} = 28\text{ V}$ ;  $I_{Dq} = 650\text{ mA}$ ;  $T_{case} = 25\text{ }^{\circ}\text{C}$ ;  
 $f = 1990\text{ MHz}$

**Fig 1. One-tone CW power gain and drain efficiency as functions of load power; typical values**



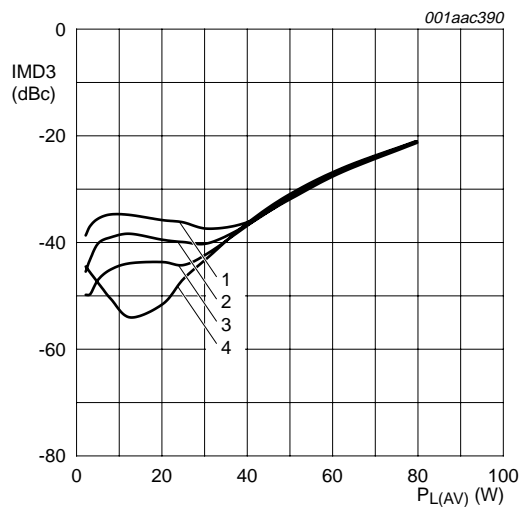
$V_{DS} = 28\text{ V}$ ;  $I_{Dq} = 650\text{ mA}$ ;  $T_{case} = 25\text{ }^{\circ}\text{C}$ ;  
 $f = 1990\text{ MHz}$

**Fig 2. Two-tone CW power gain and drain efficiency as functions of average load power; typical values**



$V_{DS} = 28\text{ V}$ ;  $I_{Dq} = 650\text{ mA}$ ;  $T_{case} = 25\text{ }^{\circ}\text{C}$ ;  
 $f = 1990\text{ MHz}$

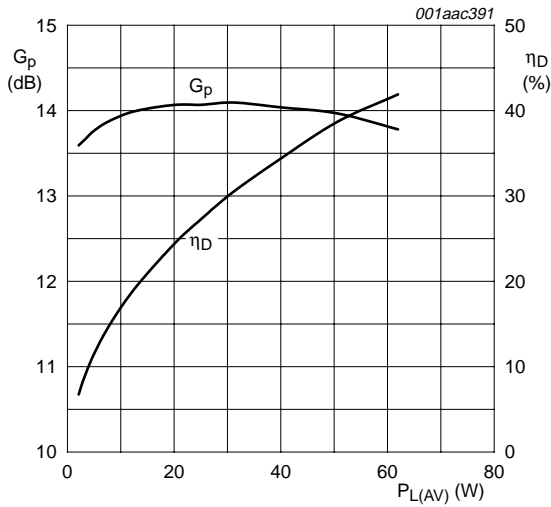
**Fig 3. Intermodulation distortion as a function of average load power; typical values**



$V_{DS} = 28\text{ V}$ ;  $T_{case} = 25\text{ }^{\circ}\text{C}$ ;  $f = 1990\text{ MHz}$

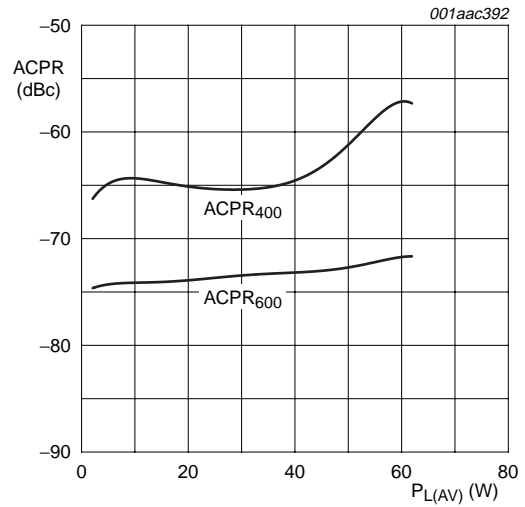
- (1)  $I_{Dq} = 550\text{ mA}$
- (2)  $I_{Dq} = 650\text{ mA}$
- (3)  $I_{Dq} = 750\text{ mA}$
- (4)  $I_{Dq} = 850\text{ mA}$

**Fig 4. Third order intermodulation distortion as a function of average load power; typical values**



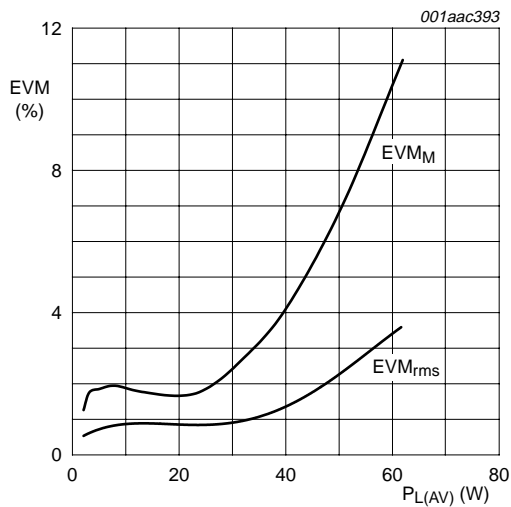
$V_{DS} = 28\text{ V}$ ;  $I_{Dq} = 650\text{ mA}$ ;  $T_{case} = 25\text{ }^\circ\text{C}$ ;  
 $f = 1990\text{ MHz}$

**Fig 5. GSM EDGE power gain and drain efficiency as functions of average load power; typical values**



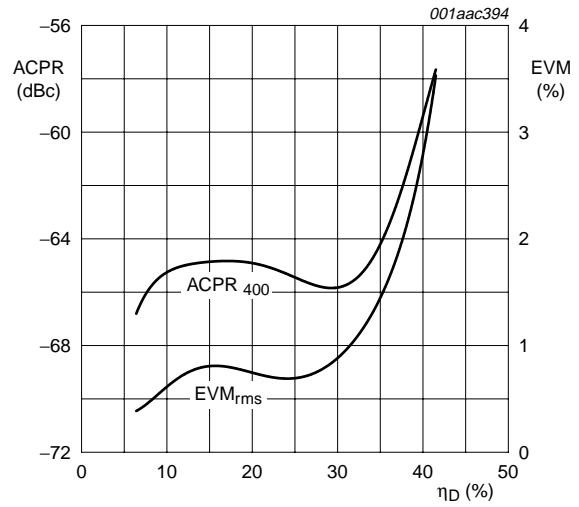
$V_{DS} = 28\text{ V}$ ;  $I_{Dq} = 650\text{ mA}$ ;  $T_{case} = 25\text{ }^\circ\text{C}$ ;  
 $f = 1990\text{ MHz}$

**Fig 6. GSM EDGE ACPR at 400 kHz and at 600 kHz as a function of average load power; typical values**



$V_{DS} = 28\text{ V}$ ;  $I_{Dq} = 650\text{ mA}$ ;  $T_{case} = 25\text{ }^\circ\text{C}$ ;  
 $f = 1990\text{ MHz}$

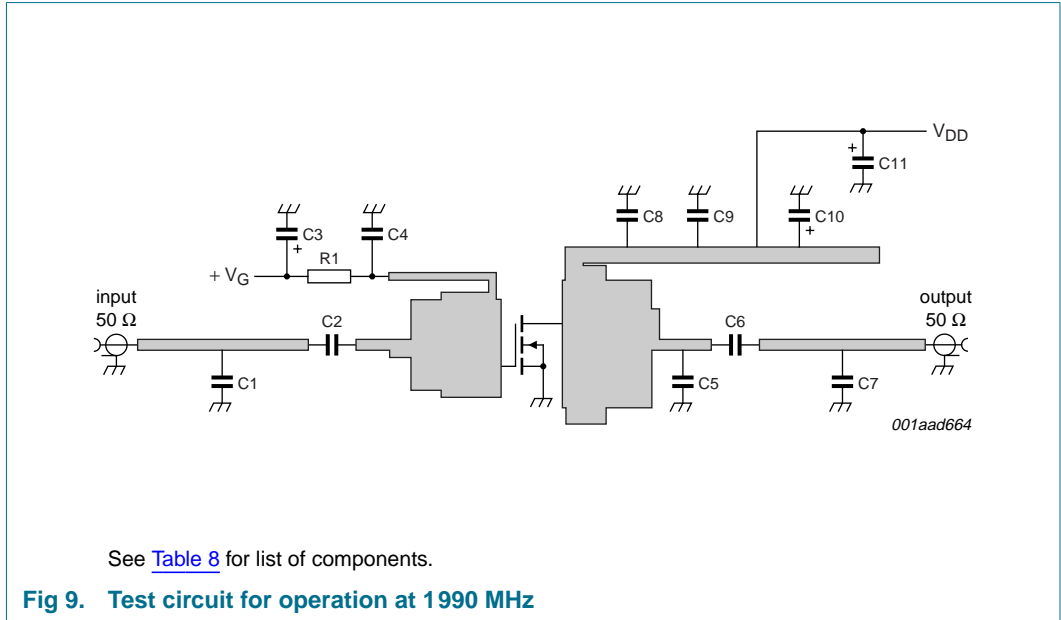
**Fig 7. GSM EDGE rms EVM and peak EVM as functions of average load power; typical values**



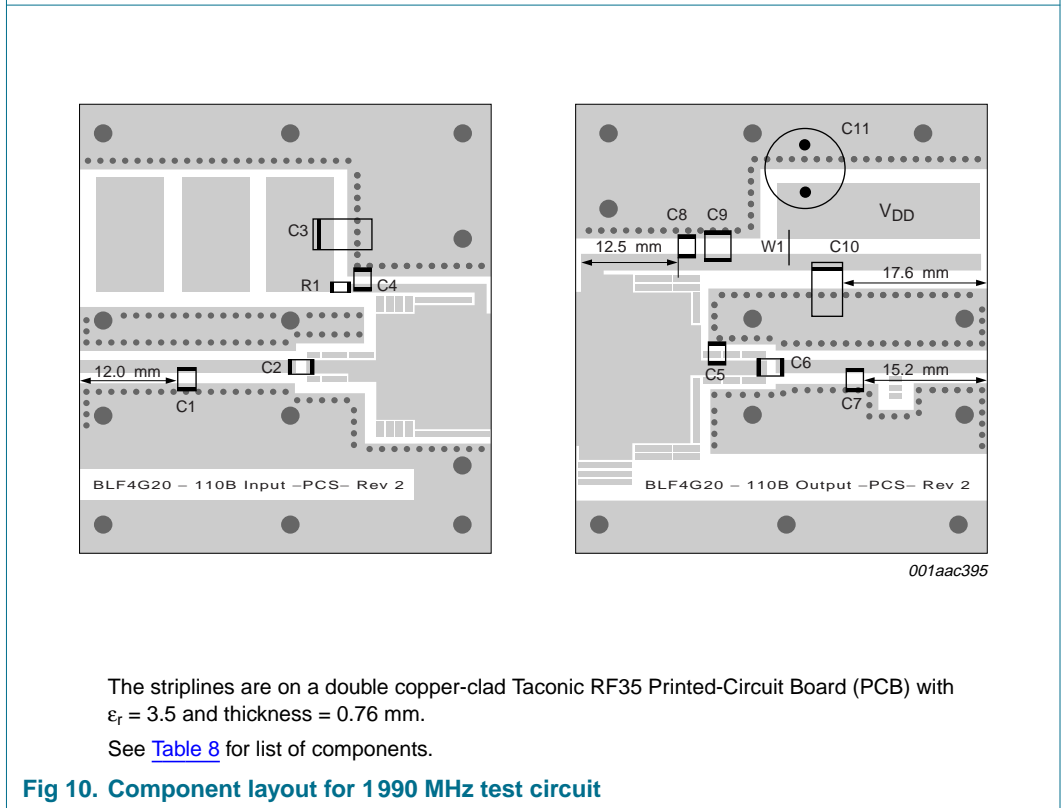
$V_{DS} = 28\text{ V}$ ;  $I_{Dq} = 650\text{ mA}$ ;  $T_{case} = 25\text{ }^\circ\text{C}$ ;  
 $f = 1990\text{ MHz}$

**Fig 8. GSM EDGE ACPR at 400 kHz and rms EVM as functions of drain efficiency; typical values**

**8. Test information**



**Fig 9. Test circuit for operation at 1990 MHz**



**Fig 10. Component layout for 1990 MHz test circuit**

Table 8: List of components (see [Figure 10](#)).

Component	Description	Value	Dimensions	Catalogue number
C1	multilayer ceramic chip capacitor	[1] 0.1 pF		
C2, C4, C8	multilayer ceramic chip capacitor	[1] 11 pF		
C3, C10	tantalum capacitor	10 $\mu$ F		
C5	multilayer ceramic chip capacitor	[1] 0.5 pF		
C6	multilayer ceramic chip capacitor	[1] 8.2 pF		
C7	multilayer ceramic chip capacitor	[1] 0.2 pF		
C9	multilayer ceramic chip capacitor	1 $\mu$ F		1812X7R105KL2AB
C11	Philips electrolytic capacitor	220 $\mu$ F; 35 V		
R1	Philips chip resistor	5.6 $\Omega$	0603	
W1	hand made wire		5 mm	

[1] American Technical Ceramics type 100B or capacitor of same quality.

**9. Package outline**

Earless flanged LDMOST ceramic package; 2 leads

SOT502B

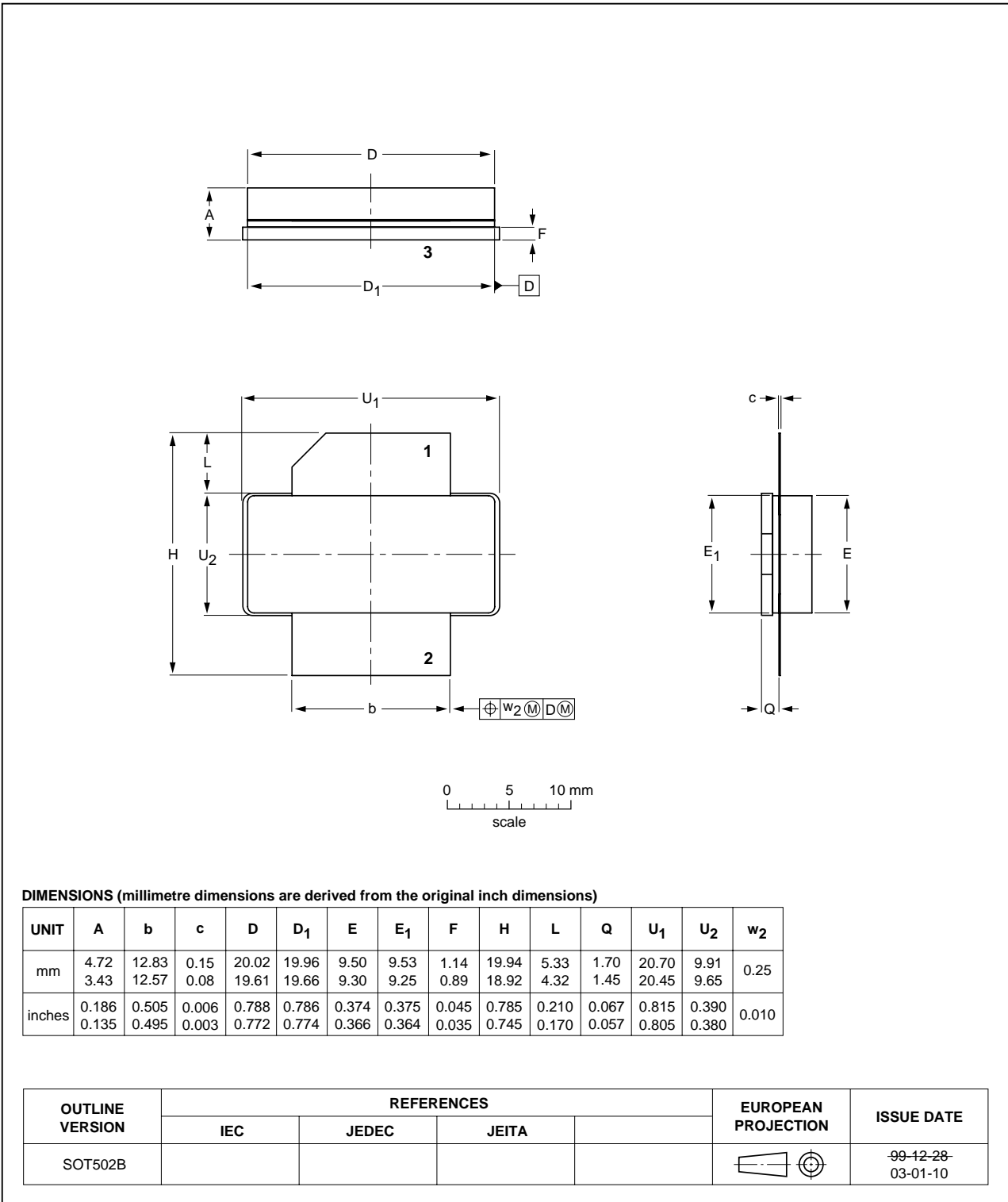


Fig 11. Package outline SOT502B



## 10. Abbreviations

Table 9: Abbreviations

Acronym	Description
ACPR	Adjacent Channel Power Ratio
CDMA	Code Division Multiple Access
CW	Continuous Wave
EDGE	Enhanced Data rates for GSM Evolution
EVM	Error Vector Magnitude
GSM	Global System for Mobile communications
$I_{Dq}$	quiescent drain current
LDMOS	Laterally Diffused Metal Oxide Semiconductor
RF	Radio Frequency
VSWR	Voltage Standing Wave Ratio

## 11. Revision history

Table 10: Revision history

Document ID	Release date	Data sheet status	Change notice	Doc. number	Supersedes
BLF4G20LS-110B_1	20060110	Product data sheet	-	9397 750 14548	-

## 12. Data sheet status

Level	Data sheet status <sup>[1]</sup>	Product status <sup>[2]</sup> <sup>[3]</sup>	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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## 17. Contents

<b>1</b>	<b>Product profile</b> .....	<b>1</b>
1.1	General description .....	1
1.2	Features .....	1
1.3	Applications .....	2
<b>2</b>	<b>Pinning information</b> .....	<b>2</b>
<b>3</b>	<b>Ordering information</b> .....	<b>2</b>
<b>4</b>	<b>Limiting values</b> .....	<b>2</b>
<b>5</b>	<b>Thermal characteristics</b> .....	<b>2</b>
<b>6</b>	<b>Characteristics</b> .....	<b>3</b>
<b>7</b>	<b>Application information</b> .....	<b>3</b>
7.1	Ruggedness in class-AB operation .....	3
<b>8</b>	<b>Test information</b> .....	<b>6</b>
<b>9</b>	<b>Package outline</b> .....	<b>8</b>
<b>10</b>	<b>Abbreviations</b> .....	<b>9</b>
<b>11</b>	<b>Revision history</b> .....	<b>10</b>
<b>12</b>	<b>Data sheet status</b> .....	<b>11</b>
<b>13</b>	<b>Definitions</b> .....	<b>11</b>
<b>14</b>	<b>Disclaimers</b> .....	<b>11</b>
<b>15</b>	<b>Trademarks</b> .....	<b>11</b>
<b>16</b>	<b>Contact information</b> .....	<b>11</b>



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